### **5LN01SP**

# ON Semiconductor®

## N-Channel Small Signal MOSFET 50V, 0.1A, 7.8 $\Omega$ , Single SPA

#### **Features**

- · Low ON-resistance
- · Ultrahigh-speed switching
- 1.5V drive

#### **Specifications**

#### Absolute Maximum Ratings at Ta=25°C

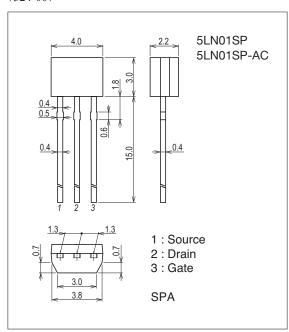
Parameter	Symbol	Conditions	Value	Unit
Drain to Source Voltage	VDSS		50	V
Gate to Source Voltage	VGSS		±10	V
Drain Current (DC)	ID		0.1	Α
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	0.4	Α
Power Dissipation	PD		0.25	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

This product is designed to "ESD immunity < 200V\*", so please take care when handling.

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

#### **Package Dimensions**

unit : mm (typ) 7524-007



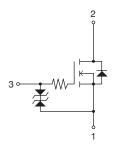
#### **Ordering & Package Information**

Device	Package	Shipping	memo	
5LN01SP	SPA SC-72	500pcs./bag	- Pb-Free	
5LN01SP-AC	SPA SC-72	2,500pcs./box		

#### **Marking**



#### **Electrical Connection**



<sup>\*</sup> Machine Model

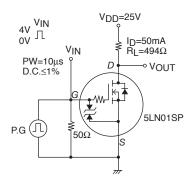
#### **5LN01SP**

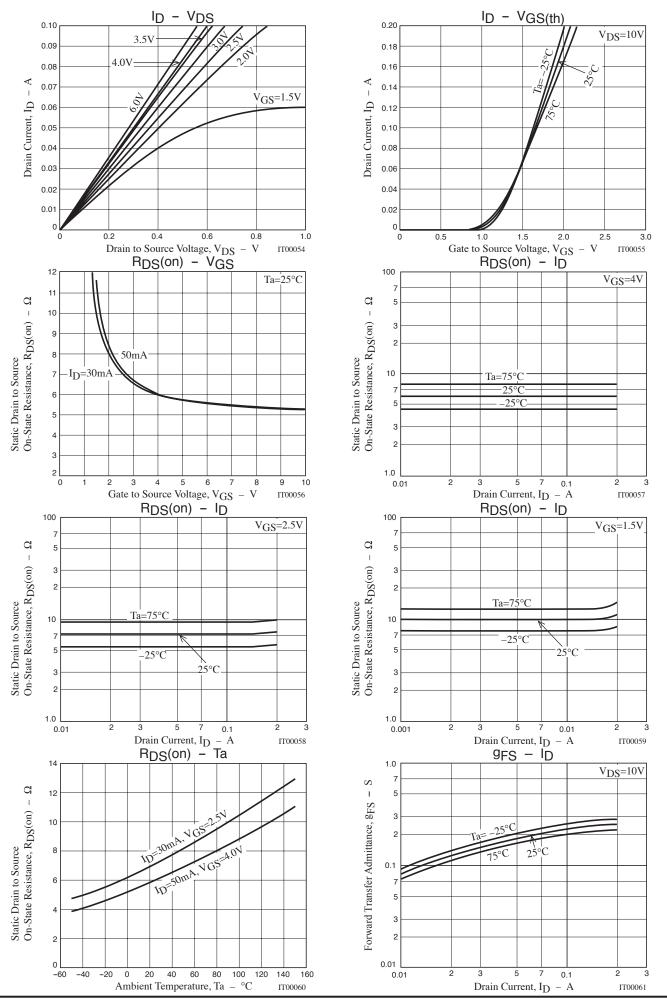
#### **Electrical Characteristics** at Ta=25°C

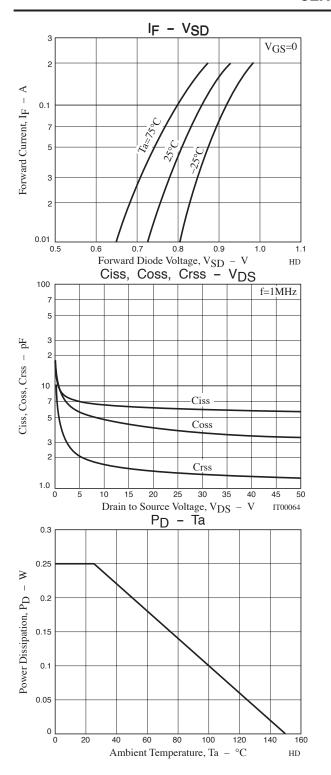
Parameter	Symbol	Conditions	Value			Unit
		Conditions	min	typ	max	Onit
Drain to Source Breakdown Voltage	V(BR)DSS	I <sub>D</sub> =1mA, V <sub>G</sub> S=0V	50			V
Zero-Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =50V, V <sub>GS</sub> =0V			10	μΑ
Gate to Source Leakage Current	IGSS	V <sub>GS</sub> =±8V, V <sub>DS</sub> =0V			±10	μΑ
Gate Threshold Voltage	VGS(th)	V <sub>DS</sub> =10V, I <sub>D</sub> =100μA	0.4		1.3	V
Forward Transconductance	9FS	V <sub>DS</sub> =10V, I <sub>D</sub> =50mA	0.13	0.18		S
Static Drain to Source On-State Resistance	RDS(on)1	ID=50mA, VGS=4V		6	7.8	Ω
	R <sub>DS</sub> (on)2	I <sub>D</sub> =30mA, V <sub>G</sub> S=2.5V		7.1	9.9	Ω
	R <sub>DS</sub> (on)3	I <sub>D</sub> =10mA, V <sub>G</sub> S=1.5V		10	20	Ω
Input Capacitance	Ciss	V <sub>DS</sub> =10V, f=1MHz		6.6		pF
Output Capacitance	Coss			4.7		pF
Reverse Transfer Capacitance	Crss			1.7		рF
Turn-ON Delay Time	t <sub>d</sub> (on)	See specified Test Circuit.		18		ns
Rise Time	tr			42		ns
Turn-OFF Delay Time	t <sub>d</sub> (off)			190		ns
Fall Time	tf			105		ns
Total Gate Charge	Qg	V <sub>DS</sub> =10V, V <sub>GS</sub> =10V, I <sub>D</sub> =100mA		1.57		nC
Gate to Source Charge	Qgs			0.20		nC
Gate to Drain "Miller" Charge	Qgd	1		0.32		nC
Forward Diode Voltage	V <sub>SD</sub>	I <sub>S</sub> =100mA, V <sub>GS</sub> =0V		0.85	1.2	V

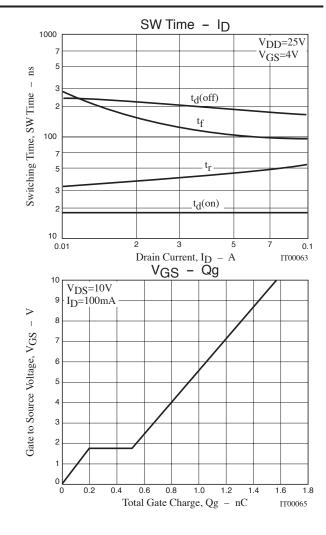
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

#### **Switching Time Test Circuit**



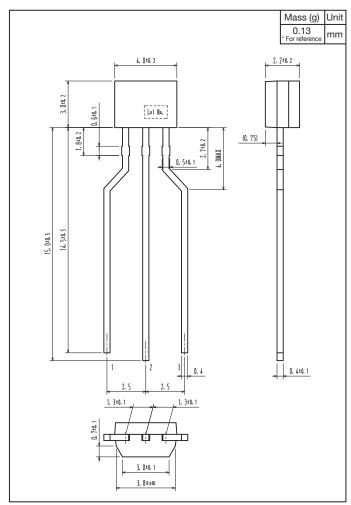






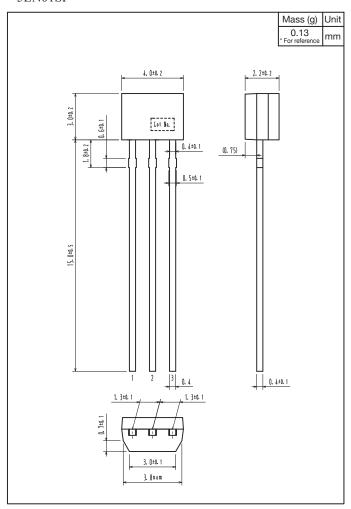
#### **Outline Drawing**

5LN01SP-AC



#### **Outline Drawing**

5LN01SP



Note on usage: Since the 5LN01SP is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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